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# Comparison of 3-bit per cell NAND Flash Memories

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By:  
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**Contents**

CONTENTS ..... III

LIST OF FIGURE ..... V

LIST OF TABLES ..... 6

EXECUTIVE SUMMARY ..... 7

INTRODUCTION ..... 8

THREE-BIT PER CELL NAND FLASH MEMORIES ..... 12

    SanDisk/Toshiba 56nm 16Gb 3-bit/cell NAND Flash Memory ..... 12

        Summary ..... 12

        Page Buffer ..... 13

        Page Organization ..... 14

        Cache algorithms ..... 15

        Source Line Bias Error Compensation ..... 17

        Power Routing Organization ..... 20

        Data Path ..... 22

    All Bitline vs. Interleaved Architecture ..... 24

        Program Speed ..... 24

        ABL - Considerations on Scalability ..... 28

    Hynix 48nm 32Gb 3-bit/cell NAND Flash Memory ..... 33

        Summary ..... 33

        Chip Architecture ..... 34

        Pass Bit Detector Circuits ..... 36

        Smart Blind Program Algorithm ..... 37

        Start Bias Controlled Program Algorithm ..... 38

    32Gb 32nm 3-bit/cell SanDisk/Toshiba ..... 40

        Summary ..... 40

        Chip Architecture ..... 41

        Program Verify Read Before Programming ..... 42

        Compact Row Decoder ..... 46

        Extended Column Architecture ..... 47

    Samsung 51nm 16Gb 3-bit/cell NAND Flash Memory ..... 48

        Summary ..... 48

        XX ..... 49

        Summary ..... 53

REFERENCES .....	57
ABOUT THE AUTHOR .....	59
ABOUT FORWARD INSIGHTS .....	60
Services .....	60
Contact .....	60
REPORT OFFERINGS .....	62

**List of Figure**

Figure 1 NAND Flash Areal Storage Density Trend .....8

Figure 2 ISPP for 2-bit and 3-bit per cell Technology ..... 11

Figure 3 ABL architecture .....13

Figure 4 Page Organization and Programming .....14

Figure 5 Conventional Cache Program ..... 15

Figure 6 FSC +MCR ..... 16

Figure 7 Source line Bias Error: Ideal Case .....17

Figure 8 Source line Bias Error: Real Case ..... 18

Figure 9 Source line Bias Error: Source Tracking .....19

Figure 10 Chip comparison .....20

Figure 11 Power Bus Routing: 16Gb D2 vs. 16Gb x3 (rotated array) .....21

Figure 12 Data Path: 16Gb D2 vs 16Gb x3 (rotated array) .....22

Figure 13 Program speed improvements .....24

Figure 14 ABL Architecture with 8K Page Size Compared to Interleaved Architecture with 4KB  
Page Size .....25

Figure 15 ABL Architecture with 8K Page Size Compared to Interleaved Architecture with 8KB  
Page Size .....26

Figure 16 ABL Architecture vs. Interleaved Architecture: Double Sided Page Buffer .....29

Figure 17 BLC Line Density vs. Core Scalability .....31

Figure 18 3-bit/cell NAND Flash Program Time .....33

Figure 19 Die micrograph of Hynix 32Gb 8LC NAND Flash Memory .....36

Figure 20 Pass Bit Detector .....37

Figure 21 Smart Blind Program .....38

Figure 22 Start Bias Controlled Program .....39

Figure 23 SanDisk/Toshiba 32nm 32Gb 3-bit/cell NAND Flash Die Micrograph .....41

Figure 24 Program Inhibit .....45

Figure 25 Schematic view of row decoder .....46

Figure 26 String Organization .....48

Figure 27 Endurance properties .....49

Figure 28 Current Degradation due to Series Resistance .....50

**List of Tables**

Table 1	Features Summary of SanDisk/Toshiba 56nm 16Gb 3-bit/cell NAND Flash Memory....	12
Table 2	ABL vs. Interleaving.....	31
Table 3	Features Summary of Hynix 48nm 32Gb 3-bit/cell NAND Flash Memory .....	34
Table 4	Features Summary of SanDisk/Toshiba 32nm 32Gb 3-bit/cell NAND Flash Memory...	40
Table 3	Features Summary of Samsung 51nm 16Gb 3-bit/cell NAND Flash Memory .....	51
Table 5	Key Parameters Comparison.....	53
Table 7	Key Features and Advantages & Disadvantages of SanDisk/Toshiba 56nm 16Gb 3-bit/cell NAND Flash Memory.....	55
Table 8	Key Features and Advantages & Disadvantages of Hynix 48nm 32Gb 3-bit/cell NAND Flash Memory .....	55
Table 9	Key Features and Advantages & Disadvantages of SanDisk/Toshiba 32nm 32Gb 3-bit/cell NAND Flash Memory.....	56
Table 10	Key Features and Advantages & Disadvantages of Samsung 51nm 16Gb 3-bit/cell NAND Flash Memory.....	56

## Executive Summary

The following is a summary of the key takeaways of this report.

- *To improve reliability and performance, SanDisk/Toshiba have implemented the XXXXXXXXXXXX for the NAND flash devices. Hynix and Samsung continue to employ the XXXXXXXXXXXXXXXXXXXX.*
- *The XXXXXXXXXXXX may face scaling challenges for future generations of NAND flash memories.*
- *Three-bit per cell endurance and retention are much lower than comparable MLC devices with retention XXXXXXXXXXXX being the norm.*
- *Programming speed for 3-bit per cell devices is slower than MLC devices due to the increasing of the number of verify levels and the ISSPP reduction. Various algorithms have been implemented to meliorate the performance degradation.*
- *The cell efficiency of the SanDisk/Toshiba and Hynix devices are XXXXXXXXXXXXXXXXXXXX whereas Samsung's first generation product is relatively XXXXXXXXXXXXXXXXXXXX.*
- *The Samsung 3-bit per cell device's specified endurance is surprisingly XXXXXXXXXXXX compared to SanDisk/Toshiba or Hynix's.*





<b>Features</b>	<b>SanDisk/ Toshiba 16Gb</b>	<b>Hynix 32Gb</b>	<b>SanDisk/ Toshiba 32Gb</b>	<b>Samsung 16Gb</b>
X Y plane size				
Pgm Speed				
Pgm Speed Features				
No. of latches/ Page Buffer				
Row Decoder				
I/O mode				
t <sub>rc</sub> (min.) / t <sub>wc</sub> (min.)				
t <sub>r</sub> (max.)				
t <sub>prog</sub> (typ.)				
t <sub>ers</sub> (typ.)				
ECC				
Endurance				
Retention				

\*Forward Insights estimates

Tables 6-10 provides an overview of some of the key technical features of the 3-bit per cell NAND flash memory devices from SanDisk/Toshiba, Hynix and Samsung as well as the advantages and disadvantages of each implementation.

Table 7 Key Features and Advantages & Disadvantages of SanDisk/Toshiba 56nm 16Gb 3-bit/cell NAND Flash Memory

SanDisk/Toshiba 56nm 16Gb 3-bit/cell NAND Flash Memory	
Key Features	Main Pros/Cons
	x
	✓
	✓
	✓

Table 8 Key Features and Advantages & Disadvantages of Hynix 48nm 32Gb 3-bit/cell NAND Flash Memory

Hynix 48nm 32Gb 3-bit/cell NAND Flash Memory	
Key Features	Main Pros/Cons
	x
	x
	x
	x
	x

Table 9 Key Features and Advantages & Disadvantages of SanDisk/Toshiba 32nm 32Gb 3-bit/cell NAND Flash Memory

SanDisk/Toshiba 32nm 32Gb 3-bit/cell NAND Flash Memory	
Key Features	Main Pros/Cons
	x
	x
	x
	✓
	x

Table 10 Key Features and Advantages & Disadvantages of Samsung 51nm 16Gb 3-bit/cell NAND Flash Memory

Samsung 51nm 16Gb 3-bit/cell NAND Flash Memory	
Key Features	Main Pros/Cons
	x
	x
	✓

## About the Author

**Luca Crippa** is Senior Technical Analyst for Design Architecture. Luca has more than 10 years of experience in **MLC flash memory design**. Previously, he was Senior Designer for 48nm floating gate and 36nm floating gate NAND flash memories at Qimonda AG as well as 90nm and 60nm MLC NAND flash products at STMicroelectronics.

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